

RB521D1-30

Schottky Diode

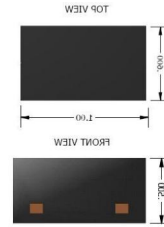
FEATURE

- Low current rectification
- Low forward voltage
- ROHS Compliant
- UL-94 V-0 / Green EMC
- Matte Tin Lead finish (Pb-Free)

MARKING:



DFN1006-2L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

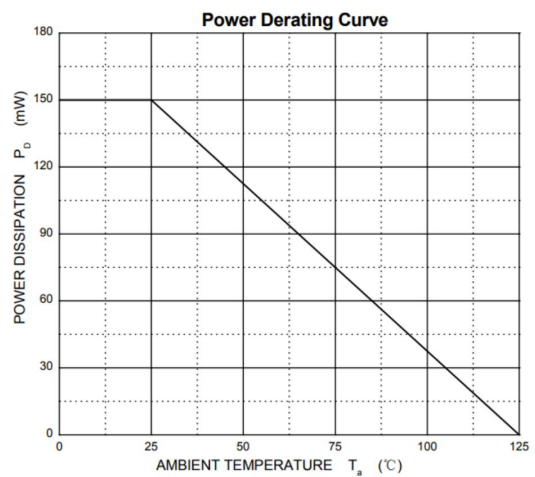
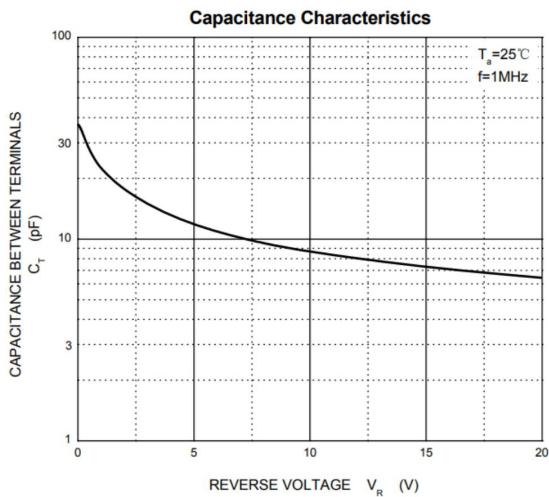
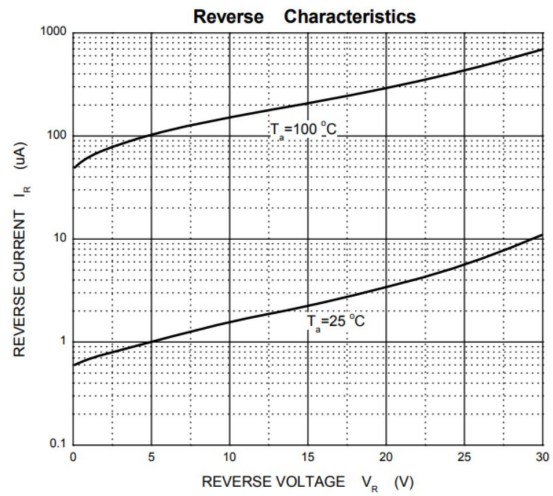
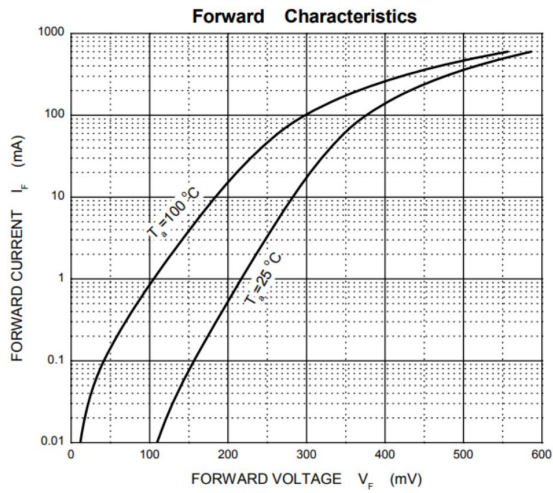
Parameter	Symbol	Value	Unit
Power Dissipation	P _D	150	mW
Reverse Voltage	V _R	30	V
Average Forward Current	I _{F(AV)}	200	mA
Non-Repetitive Peak Forward Current *1	I _{FSM}	500	mA
Junction Temperature	T _J	125	°C
Storage Temperature	T _{STG}	-55 to +125	°C

*1: Pulse width = 1 μs

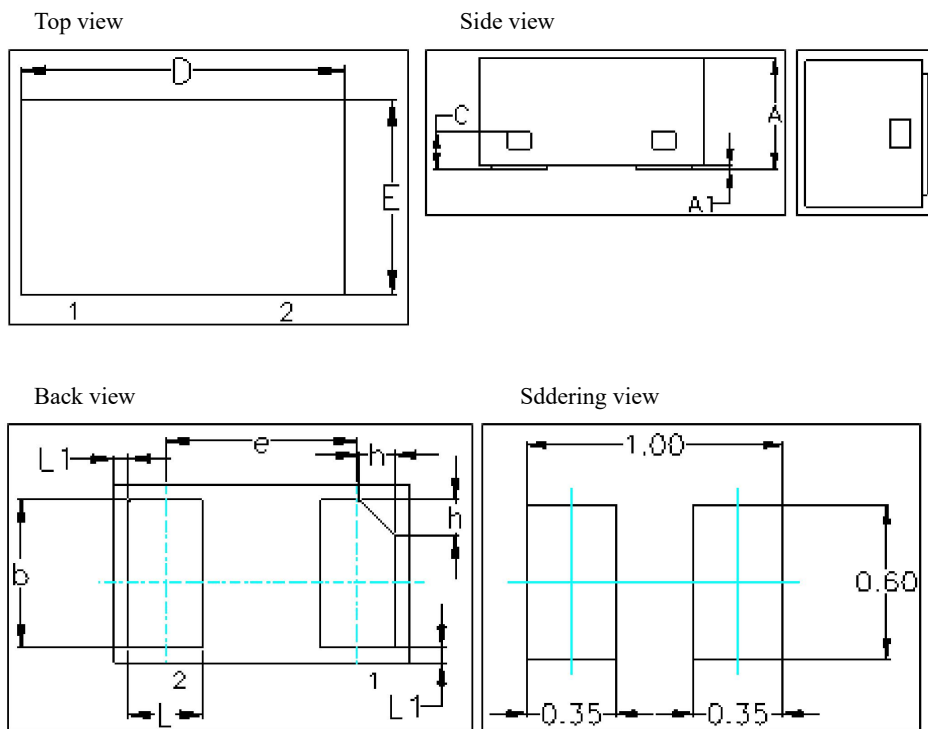
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse Leakage Current	I _R	V _R =10V			30	uA
Forward Voltage	V _F	I _F =10mA			0.35	V
		I _F =200mA			0.5	
Reverse Voltage	V _R	I _R =100uA	30			V

Typical Electrical and Thermal Characteristics



DFN1006-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	0.45	0.50	0.55
A1	0.00	0.02	0.05
b	0.45	0.50	0.55
C	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65 BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05 REF.		
h	0.07	0.12	0.17

1. Unit mm